

~~8/b~~ Claims

1. Method for rotating a disc-shaped object (10), such as a wafer, wherein along a side of said object a gas flow is guided, giving a rotation to said object, wherein said gas flow is given the rotation generating component being tangential to said object by a pattern of grooves, characterised in that, said object is floatingly received in a compartment being closed on all sides, said object being substantially rotating only and in that along the other side of said object, a further gas flow is directed.
2. Method according to claim 1, wherein said disc shaped object is provided substantially horizontal and said rotation generating gas flow is introduced at the upper side of said disc shaped object.
3. Method according to Claim 1 or 2, characterised in that the said at least one gas flow is controlled using a pattern of spiral grooves.
4. Method according to Claim 3, wherein the origin of the spiral lies in the vicinity of the desired centre (11) of the wafer, and the end of the spiral lies in the vicinity of the desired circumferential edge of the wafer.
5. Method according to Claim 1, wherein the said at least one gas flow is controlled using a pattern of grooves, which pattern of grooves comprises circle segments, and at least one gas-introduction opening is arranged in the vicinity of the said circle segments.
6. Method according to Claim 5, in wherein at least one gas-discharge opening is arranged in the vicinity of the said circle segments.
7. Method according to one of the preceding claims, wherein the wafer is rotated at 2-100 rpm.
8. ~~8/b~~ Reactor (1) for the floating, rotational treatment of semiconductor wafers, comprising a top part (2) and a bottom part (3), between which a chamber (12) which accommodates the wafer is delimited, the said top part and bottom part being provided with gas-supply openings, characterised in that a pattern of grooves (9, 19) is arranged in at least one of the said parts, said pattern of grooves imparts to the said gas flow a component which is tangential with respect to the said object.
9. Reactor according to Claim 8, wherein the gas-introduction openings (4, 14, 16) extend essentially perpendicular to the top part (2) and/or bottom part (3).
10. Reactor according to Claim 8 or 9, wherein the said pattern of grooves comprises a pattern of spiral-shaped grooves (9).

11. Reactor according to Claim 10, wherein, in at least one of the said parts, the said gas-supply openings (4) are arranged along a spiral line (8).
12. Reactor according to Claim 10 or 11, wherein the origin of the said spiral lies in the vicinity of the desired centre (11) of the wafer (10), and the end of the said spiral lies in the vicinity of the desired circumferential edge of the wafer.
13. Reactor according to one of Claims 11 or 12, wherein the said supply openings (4) are arranged next to the said spiral grooves (9).
14. Reactor according to one of Claims 11-13, wherein the said spiral grooves are designed so as to widen in the direction of flow.
- 10 15. Reactor according to Claim 8, wherein the said pattern of grooves comprises circle segments (19), and at least one gas-introduction opening is arranged in the vicinity of the said circle segments.
16. Reactor according to Claim 15, wherein at least one gas-discharge opening is arranged in the vicinity of the said circle segments.